

210  
line 14, after "more" add -) able to absorb crystal  
defects and prevent defect migration and extension--;

line 15, delete "fragile, or soft,";

line 17, change "across" to --otherwise cross--;

line 19, change "restricts expansion" to --restricts  
the extension of migration--;

line 22, change "by" to --from--.

#### IN THE CLAIMS

Please amend Claims 1, 2, and 4-7 and add new Claims 8-10  
as follows:

--1. (Amended) A semiconductor light emitting device  
comprising:

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a hetero-configuration having an active layer that emits  
light when charge carriers are injected, a first clad layer,  
and a second clad layer, the active layer being interposed  
between the clad layers, the first and second clad layers  
keeping the injected charge carriers in the active layer;

a first and a second electrode, the layers of the hetero-  
configuration being interposed between the electrodes; and

a first dense [defect-injected] defect layer[,] provided  
between the first electrode and the layers of the hetero-  
configuration, the first dense [defect-injected] defect layer

being made of a material [being more fragile than the hetero-configuration, the first dense defect-injected layer preventing defects injected into] having a concentration of crystal defects, a value of a lattice constant, and a thickness which together prevent at least some of the crystal defects generated remotely from the layers of the hetero-configuration from reaching the layers of the hetero-configuration.

2. (Amended) the device according to claim 1, further comprising a second dense [defect-injected] defect layer[,] provided between the second electrode and the layers of the hetero-configuration, the second dense [defect-injected] defect layer being made of a material [being more fragile than the hetero-configuration, the second dense defect-injected layer preventing defects injected into] having a concentration of crystal defects, a value of a lattice constant, and a thickness which together prevent at least some of the crystal defects generated remotely from the layers of the hetero-configuration from reaching the layers of the hetero-configuration.--

Claim 4, line 3, change "defect-injected" to --defect--.

--5. (Amended) The device according to claim 1, further comprising a semiconductor substrate provided between the

second electrode and the layers of the hetero-configuration and a buffer layer provided on the semiconductor substrate [that prevents], said buffer layer helping to impede remotely generated crystal defects [being generated in the semiconductor substrate or prevents the defects being expanded into] from reaching the active layer.

6. (Amended) ~~A semiconductor light emitting device comprising:~~

~~a hetero-configuration having an active layer that emits light when charge carriers are injected, a first clad layer, and a second clad layer, the active layer being interposed between the clad layers, the first and second clad layers keeping the injected charge carriers in the active layer;~~

~~a first and a second electrode, the layers of the hetero-configuration being interposed between the electrodes; [and]~~

~~a dense [defect-injected] defect layer[,] provided between the first electrode and the layers of the hetero-configuration, the dense [defect-injected] defect layer being made of a material [being more fragile than the hetero-configuration, the dense defect-injected layer preventing defects injected into] having a concentration of crystal defects, a value of a lattice constant and a thickness which together prevent at least some of the crystal defects~~

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Sub. B3  
7  
generated remotely from the layers of the hetero-configuration  
from reaching the layers of the hetero-configuration,

a current diffusion layer[,] provided between the first electrode and the dense [defect-injected] defect layer, the current diffusion layer diffusing current applied through the first electrode;

A12  
cont  
a contact layer[,] provided between the first electrode and the current diffusion layer, the contact layer making ohmic contact between the first electrode and the current diffusion layer;

a semiconductor substrate[,] provided between the second electrode and the layers of the hetero-configuration;

a buffer layer[,] provided on the semiconductor substrate, the buffer layer [preventing defects being generated in the semiconductor substrate or prevents the defects being expanded into] helping to impede remotely generated crystal defects from reaching the active layer; and

a reflective layer[,] provided on the buffer layer, the reflective layer reflecting light emitted by the active layer so that the emitted light does not enter the buffer layer and the semiconductor substrate.

7. (Amended) A semiconductor light emitting device comprising:

Fig. 10 B2  
a hetero-configuration having an active layer that emits light when charge carriers are injected, a first clad layer and a second clad layer, the active layer being interposed between the clad layers, the first and second clad layers keeping the injected charge carriers in the active layer;

a first and a second electrode, the layers of the hetero-configuration being interposed between the electrodes;

A12  
cont  
a first dense [defect-injected] defect layer[,] provided between the first electrode and the layers of the hetero-configuration, the first dense [defect-injected] defect layer being made of a material [being more fragile than the hetero-configuration, the first dense defect-injected layer preventing defect injected into] having a concentration of crystal defects, a value of a lattice constant and a thickness which together prevent at least some of the crystal defects generated remotely from the layers of the hetero-configuration from reaching the layers of the hetero-configuration;

a current diffusion layer[,] provided between the first electrode and the first dense [defect-injected] defect layer, the current diffusion layer diffusing current applied through the first electrode;

a contact layer[,] provided between the first electrode and the current diffusion layer, the contact layer making ohmic

contact between the first electrode and the current diffusion layer;

a second dense [defect-injected] defect layer[,] provided between the second electrode and the layers of the hetero-configuration, the second dense [defect-injected] defect layer being made of a material [being more fragile than the hetero-configuration, the second dense defect-injected layer preventing defects injected into] having a concentration of crystal defects, a value of a lattice constant and a thickness which together prevent at least some of the crystal defects generated remotely from the layers of the hetero-configuration from reaching the layers of the hetero-configuration; and

a buffer layer[,] provided on the second electrode, the buffer layer [preventing defects being generated in the semiconductor substrate or prevents the defects being expanded into] helping to impede remotely generated crystal defects from reaching the active layer.

8. The device according to claim 1, wherein the concentration of crystal defects is  $10^4/\text{cm}^2$  or greater, the value of the lattice constant is  $10^{-2}$  or greater, and the thickness of the first dense layer is 10nm or greater.

9. The device according to claim 6, wherein the minimum concentration of crystal defects is  $10^4/\text{cm}^2$  or greater, the

value of the lattice constant is  $10^{-2}$  or greater, and the thickness of the first dense layer is 10nm or greater.

10. The device according to claim 7, wherein both of the minimum concentrations of crystal defects are  $10^4/\text{cm}^2$  or greater, both of the minimum values of lattice constants are  $10^{-2}$  or greater, and the thickness of the first and the second dense layers is 10nm or greater.--

IN THE ABSTRACT OF THE DISCLOSURE

Page 18, line 13, delete "-";

lines 14-16, delete in their entirety and replace with the following:

--layer is made of a material having a concentration of crystal defects, a value of a lattice constant and a thickness which together help prevent at least some remotely generated crystal defects from reaching the layers of the hetero-configuration.--

REMARKS

Favorable reconsideration of this application, as amended, is respectfully requested.

Claims 1-10 are now present in this application. Claims 1, 2, and 4-7 have been amended while Claims 8-10 have been added without the introduction of any new matter.